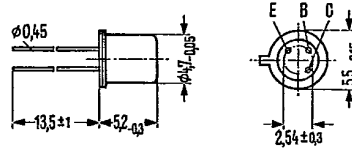


PNP Silicon Planar Transistors 2 N 2906 A
2 N 2907 A
SIEMENS AKTIENGESELLSCHAFT **T-37-17**

2 N 2906 A and 2 N 2907 A are epitaxial PNP silicon planar transistors in TO 18 case (18 A 3 DIN 41876). The collector is electrically connected to the case. The transistors are particularly suitable for use as high-speed switches.

Type	Ordering code
2 N 2906 A	Q62702-F408
2 N 2907 A	Q62702-S170



Approx. weight 0.3 g Dimensions in mm

Maximum ratings

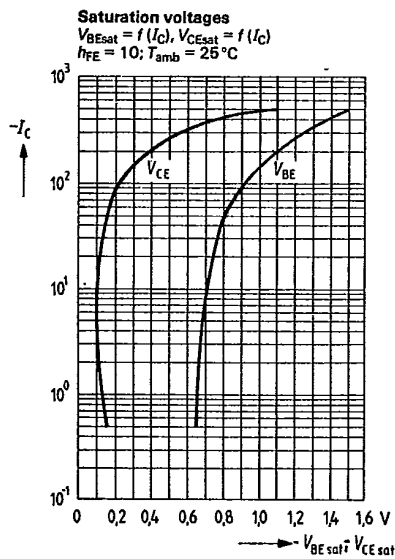
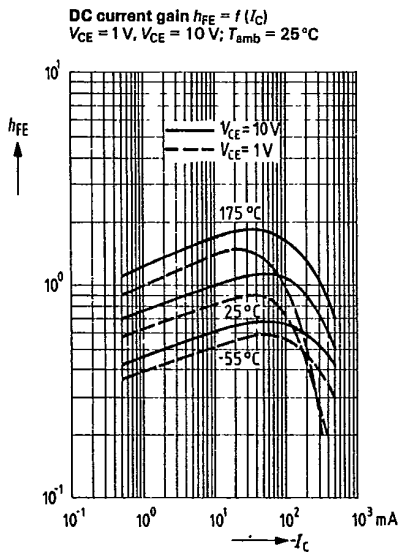
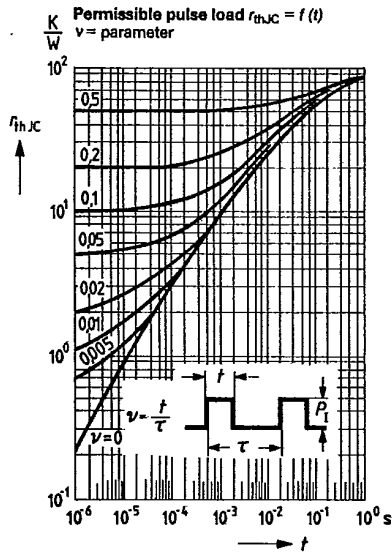
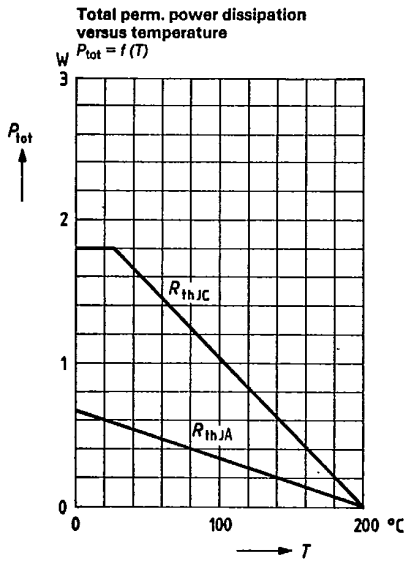
	2 N 2906 A 2 N 2907 A	
Collector-emitter voltage	-V _{CEO} 60	V
Collector-base voltage	-V _{CBO} 60	V
Emitter-base voltage	-V _{EBO} 5	V
Collector current	-I _C 0.6	A
Junction temperature	T _J 200	°C
Storage temperature range	T _{stg} -65 to +200	°C
Total power dissipation (T _{amb} = 25 °C)	P _{tot} 0.4	W
Total power dissipation (T _{case} = 25 °C)	P _{tot} 1.8	W

Thermal resistance

Junction to ambient air	R _{thJA} < 438	K/W
Junction to case	R _{thJC} < 97	K/W

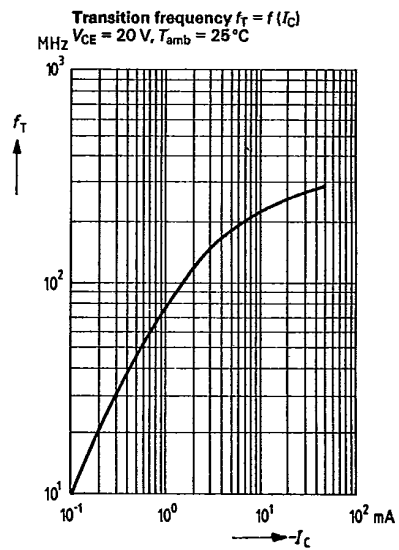
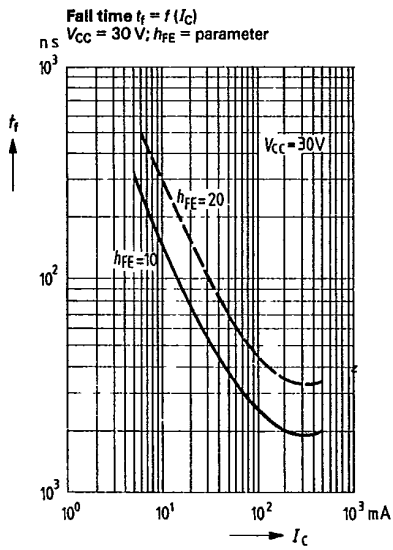
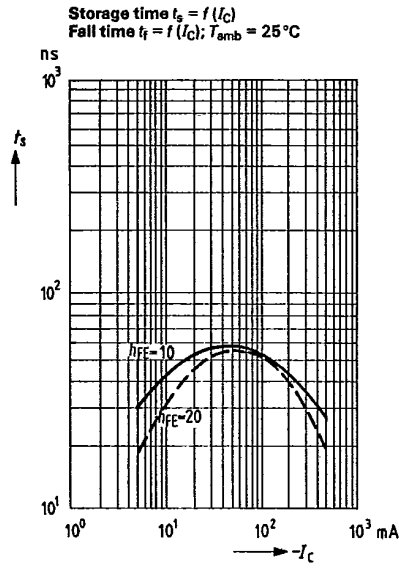
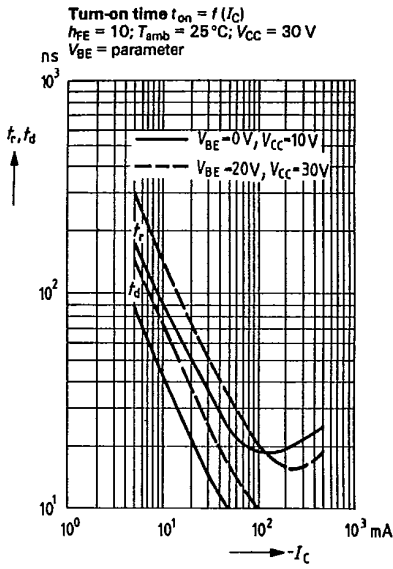
Static characteristics ($T_{amb} = 25\text{ }^\circ\text{C}$)		2 N 2906 A	2 N 2907 A	
Collector-base breakdown voltage ($-I_C = 10\text{ }\mu\text{A}$)	$-V_{(BR)CBO}$	> 60	> 60	V
Collector-emitter breakdown voltage ($-I_C = 10\text{ mA}$)	$-V_{(BR)CEO}$	> 60	> 60	V
Emitter-base breakdown voltage ($-I_E = 10\text{ }\mu\text{A}$)	$-V_{(BR)EBO}$	> 5	> 5	V
Collector-emitter saturation voltage ($-I_B = 15\text{ mA}; -I_C = 150\text{ mA}$)	$-V_{CEsat}$	< 0.4	< 0.4	V
($-I_B = 50\text{ mA}; -I_C = 500\text{ mA}$)	$-V_{CEsat}$	< 1.6	< 1.6	V
Base-emitter saturation voltage ($-I_C = 150\text{ mA}; -I_B = 15\text{ mA}$)	$-V_{BEsat}$	< 1.3	< 1.3	V
($-I_C = 500\text{ mA}; -I_B = 50\text{ mA}$)	$-V_{BEsat}$	< 2.6	< 2.6	V
Collector cutoff current ($-V_{CB} = 50\text{ V}$)	$-I_{CBO}$	< 10	< 10	nA
($-V_{CB} = 50\text{ V}; T_{amb} = 150\text{ }^\circ\text{C}$)	$-I_{CBO}$	< 10	< 10	μA
DC current gain ($-V_{CE} = 10\text{ V}; -I_C = 100\text{ }\mu\text{A}$)	h_{FE}	> 40	> 75	-
($-V_{CE} = 10\text{ V}; -I_C = 1\text{ mA}$)	h_{FE}	> 40	> 100	-
($-V_{CE} = 10\text{ V}; -I_C = 10\text{ mA}$)	h_{FE}	> 40	> 100	-
($-V_{CE} = 10\text{ V}; -I_C = 150\text{ mA}$)	h_{FE}	40 to 120	100 to 300	-
($-V_{CE} = 10\text{ V}; -I_C = 500\text{ mA}$)	h_{FE}	> 40	> 50	-
Dynamic characteristics ($T_{amb} = 25\text{ }^\circ\text{C}$)				
Collector-base capacitance ($-V_{CB} = 10\text{ V}; f = 100\text{ kHz}$)	C_{CBO}	< 8	< 8	pF
Transition frequency ($-V_{CE} = 20\text{ V}; -I_C = 50\text{ mA}; f = 100\text{ MHz}$)	f_T	> 200	> 200	MHz
Switching times:				
($-V_{CC} = 30\text{ V}; -I_C = 150\text{ mA};$ I_{B1} approx. $-I_{B2}$ approx. 15 mA)				
Delay time	t_d	< 10	< 10	ns
Rise time	t_r	< 40	< 40	ns
Storage time	t_s	< 80	< 80	ns
Fall time	t_f	< 30	< 30	ns

2 N 2906
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